ITES

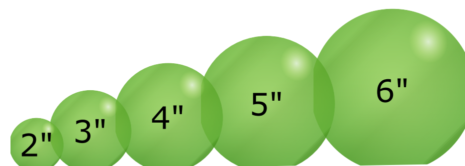
SiC wafer crystal
defect inspection & analysis service

Various service menus provided

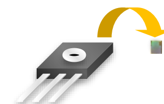
We will optimize the observation conditions according to various customer needs such as sample forms, target defect types, and the purpose of observation, etc.
Please feel free to contact us.

Observation target:

● Wafer
Target size: 2 to 6 inches



* We can meet various requirements: Only want to see some specific areas on wafer, individually cut pieces of wafer, etc.



● Packaged Module

Before PL observation, open the package, expose the chip surface, and remove the metal electrodes.

Observation wavelength:

You can select the observation wavelength according to the types of defects you want to see.

Observation Wavelength	Target defect types
> 700 nm	BPD, triangular defect, micropipe
420 nm	SF (single Shockley type)
500 nm	SF (double Shockley type)
380 nm	BPD (in drift layer, in buffer layer)

Observation field of view:

You can choose from two sizes of field of view.

Objective Lens	Field of View	Resolution (Pixel resolution)
x5	2.66 mm□	2.6 μm/pixel
x10	1.33 mm□	1.3 μm/pixel

* Details of the observation conditions will be decided by the meeting with the requester before start of observation

Contact: SiC@ites.co.jp

Passion for Truth ITES